

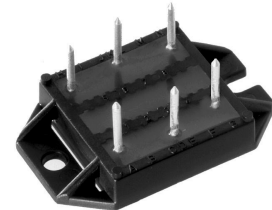
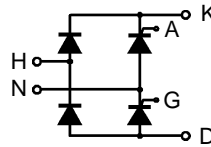
Single Phase Rectifier Bridge

$$I_{dAV} = 36 \text{ A}$$

$$V_{RRM} = 800-1600 \text{ V}$$

Preliminary data

V_{RSM} V_{DSM} V	V_{RRM} V_{DRM} V	Type
900	800	VGO 36-08io7
1300	1200	VGO 36-12io7
1500	1400	VGO 36-14io7
1700	1600	VGO 36-16io7



Symbol	Test Conditions	Maximum Ratings	Features
I_{dAV} ①	$T_H = 85^\circ\text{C}$, module	36 A	<ul style="list-style-type: none"> • Package with DCB ceramic base plate • Isolation voltage 3000 V~ • Planar passivated chips • Low forward voltage drop • Leads suitable for PC board soldering
I_{dAVM} ①	module	40 A	
I_{FRMS} , I_{TRMS}	per leg	31 A	
I_{FSM} , I_{TSM}	$T_{VJ} = 45^\circ\text{C}$; $V_R = 0 \text{ V}$	$t = 10 \text{ ms}$ (50 Hz), sine $t = 8.3 \text{ ms}$ (60 Hz), sine	320 A 350 A
	$T_{VJ} = T_{VJM}$ $V_R = 0 \text{ V}$	$t = 10 \text{ ms}$ (50 Hz), sine $t = 8.3 \text{ ms}$ (60 Hz), sine	280 A 310 A
I^2t	$T_{VJ} = 45^\circ\text{C}$ $V_R = 0 \text{ V}$	$t = 10 \text{ ms}$ (50 Hz), sine $t = 8.3 \text{ ms}$ (60 Hz), sine	500 A ² s 520 A ² s
	$T_{VJ} = T_{VJM}$ $V_R = 0 \text{ V}$	$t = 10 \text{ ms}$ (50 Hz), sine $t = 8.3 \text{ ms}$ (60 Hz), sine	390 A ² s 400 A ² s
$(di/dt)_{cr}$	$T_{VJ} = 125^\circ\text{C}$ $f = 50 \text{ Hz}$, $t_p = 200 \mu\text{s}$ $V_D = 2/3 V_{DRM}$ $I_G = 0.3 \text{ A}$, $di_G/dt = 0.3 \text{ A}/\mu\text{s}$	repetitive, $I_T = 50 \text{ A}$	150 A/ μs
	$T_{VJ} = T_{VJM}$; $V_{DR} = 2/3 V_{DRM}$ $R_{GK} = \infty$; method 1 (linear voltage rise)	non repetitive, $I_T = 1/2 \cdot I_{dAV}$	500 A/ μs
$(dv/dt)_{cr}$			1000 V/ μs
V_{RGM}			10 V
P_{GM}	$T_{VJ} = T_{VJM}$ $I_T = I_{TAVM}$	$t_p = 30 \mu\text{s}$	$\leq 10 \text{ W}$
		$t_p = 500 \mu\text{s}$	$\leq 5 \text{ W}$
		$t_p = 10 \text{ ms}$	$\leq 1 \text{ W}$
P_{GAVM}			0.5 W
T_{VJ}			-40...+125 °C
T_{VJM}			125 °C
T_{stg}			-40...+125 °C
V_{ISOL}	50/60 Hz, RMS	$t = 1 \text{ min}$	2500 V~
	$I_{ISOL} \leq 1 \text{ mA}$	$t = 1 \text{ s}$	3000 V~
M_d	Mounting torque (M4)		1.5 - 2 Nm
			14 - 18 lb.in.
Weight	typ.		18 g

Data according to IEC 60747 refer to a single diode/thyristor unless otherwise stated
① for resistive load at bridge output. IXYS reserves the right to change limits, test conditions and dimensions.

Symbol	Test Conditions	Characteristic Values
I_R, I_D	$V_R = V_{RRM}, V_D = V_{DRM}$ $T_{VJ} = T_{VJM}$ $T_{VJ} = 25^\circ\text{C}$	≤ 5 mA ≤ 0.3 mA
V_T, V_F	$I_T, I_F = 45$ A; $T_{VJ} = 25^\circ\text{C}$	≤ 1.45 V
V_{TO}	For power-loss calculations only ($T_{VJ} = 125^\circ\text{C}$)	0.85 V
r_T		13 m Ω
V_{GT}	$V_D = 6$ V; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	≤ 1.0 V ≤ 1.2 V
I_{GT}	$V_D = 6$ V; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	≤ 65 mA ≤ 80 mA ≤ 50 mA
V_{GD}	$T_{VJ} = T_{VJM};$ $V_D = 2/3 V_{DRM}$	≤ 0.2 V
I_{GD}	$T_{VJ} = T_{VJM};$ $V_D = 2/3 V_{DRM}$	≤ 5 mA
I_L	$I_G = 0.3$ A; $t_G = 30$ μs ; $di_G/dt = 0.3$ A/ μs ; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	≤ 150 mA ≤ 200 mA ≤ 100 mA
I_H	$T_{VJ} = 25^\circ\text{C}$; $V_D = 6$ V; $R_{GK} = \infty$	≤ 100 mA
t_{gd}	$T_{VJ} = 25^\circ\text{C}$; $V_D = 1/2 V_{DRM}$ $I_G = 0.3$ A; $di_G/dt = 0.3$ A/ μs	≤ 2 μs
t_q	$T_{VJ} = 125^\circ\text{C}$; $I_T = 15$ A; $t_p = 300$ μs ; $V_R = 100$ V $di/dt = -10$ A/ μs ; $dv/dt = 20$ V/ μs ; $V_D = 2/3 V_{DRM}$	typ. 150 μs
R_{thJC}	per thyristor (diode); DC current per module	1.4 K/W 0.35 K/W
R_{thJK}	per thyristor (diode); DC current per module	2.0 K/W 0.5 K/W
d_s	Creepage distance on surface	12.6 mm
d_A	Creepage distance in air	6.3 mm
a	Max. allowable acceleration	50 m/s ²

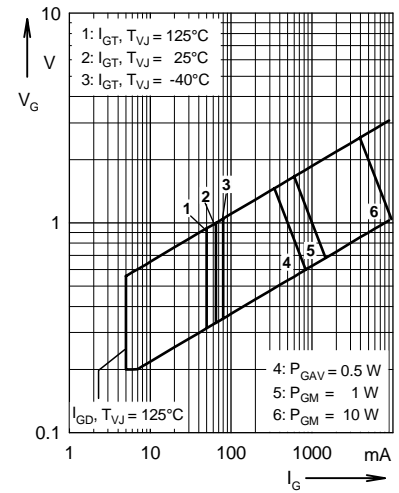


Fig. 1 Gate trigger range

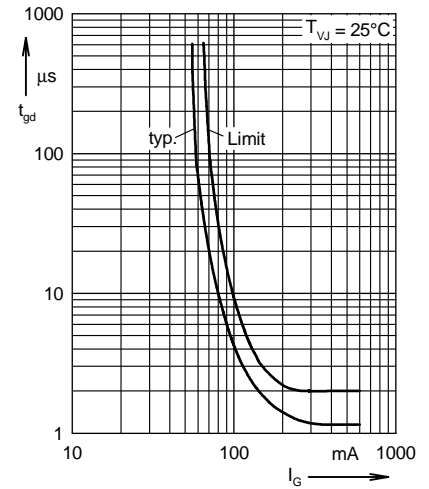


Fig. 2 Gate controlled delay time t_{gd}

Dimensions in mm (1 mm = 0.0394")

